



## Digital transistors (built-in resistors)

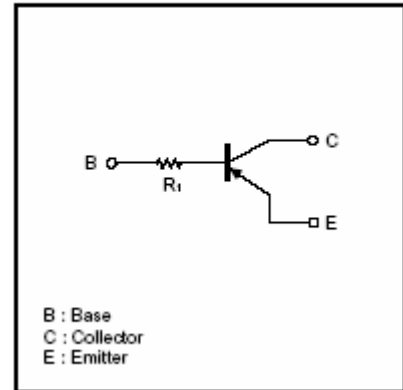
### DTA114TE/ DTA114TUA /DTA114TCA/ DTA114TKA/ DTA114TSA

TRANSISTOR (PNP)

#### FEATURES

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors.
- The bias resistors consist of thin-film resistors with complete isolation to without connecting external input. They also have the advantage of almost completely eliminating parasitic effects.
- Only the on/off conditions need to be set for operation, marking device design easy.

#### ●Equivalent circuit



#### PIN CONNECTIONS AND MARKING

<p>DTA114TE</p> <p>(1) Base (2) Emitter (3) Collector</p> <p>SOT-523      Abbreviated symbol: 94</p>	<p>DTA114TUA</p> <p>(1) Base (2) Emitter (3) Collector</p> <p>SOT-323      Abbreviated symbol: 94</p>
<p>DTA114TKA</p> <p>(1) Base (2) Emitter (3) Collector</p> <p>SOT-23-3L      Abbreviated symbol: 94</p>	<p>DTA114TCA</p> <p>(1) Base (2) Emitter (3) Collector</p> <p>SOT-23      Abbreviated symbol: 94</p>
<p>DTA114TSA</p> <p>(1) Emitter (2) Collector (3) Base</p> <p>TO-92S</p>	

**MAXIMUM RATINGS\***  $T_A=25^{\circ}\text{C}$  unless otherwise noted

Symbol	Parameter	LIMITS(DTA114T□)					Units
		E	UA	KA	CA	SA	
$V_{CBO}$	Collector-Base Voltage	-50					V
$V_{CEO}$	Collector-Emitter Voltage	-50					V
$V_{EBO}$	Emitter-Base Voltage	-5					V
$I_C$	Collector Current -Continuous	-100					mA
$P_C$	Collector Dissipation	150	200			300	mW
$T_J, T_{stg}$	Junction and Storage Temperature	-55~+150					$^{\circ}\text{C}$

**ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}\text{C}$  unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu\text{A}, I_E=0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-50\text{V}, I_E=0$			-0.5	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-4\text{V}, I_C=0$			-0.5	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=-5\text{V}, I_C=-1\text{mA}$	100	250	600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-10\text{mA}, I_B=-1\text{mA}$			-0.3	V
Transition frequency	$f_T$	$V_{CE}=-10\text{V}, I_C=-5\text{mA}, f=100\text{MHz}$		250		MHz
Input resistor	R1		7	10	13	$k\Omega$

**Typical Characteristics**

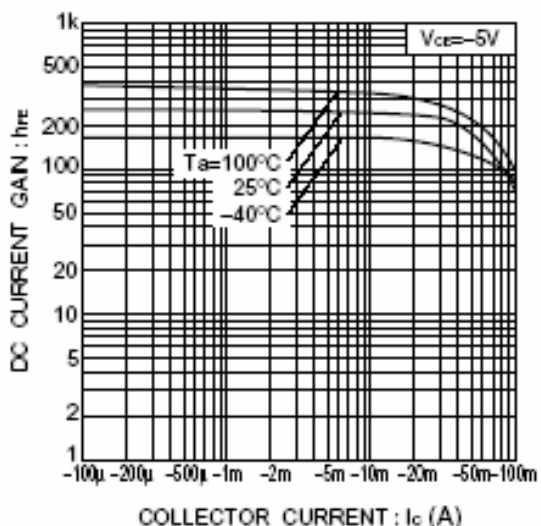


Fig.1 DC current gain vs. collector current

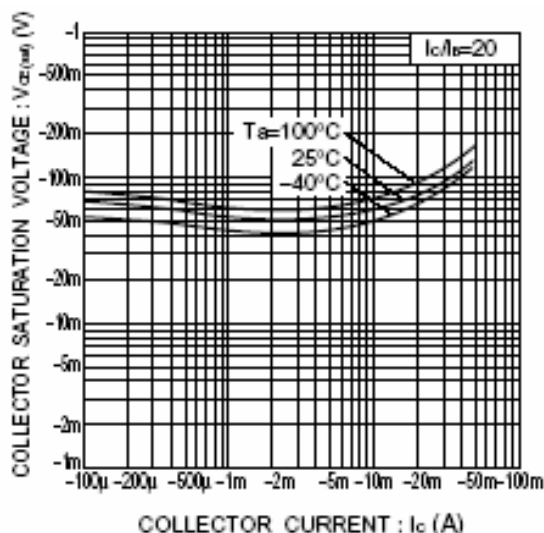


Fig.2 Collector-emitter saturation voltage vs. collector current